

TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

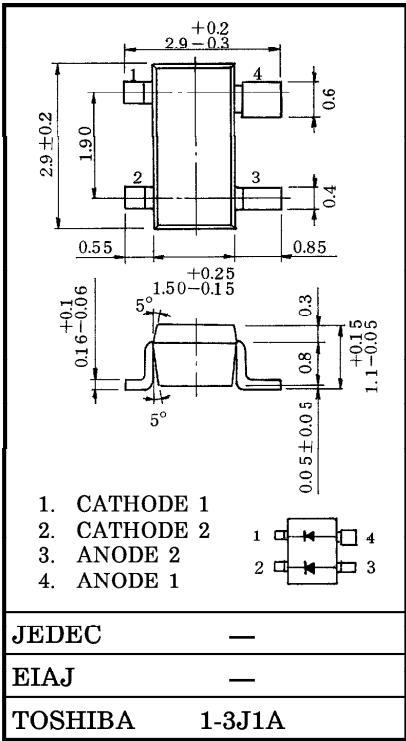
1SV237

VHF~UHF BAND RF ATTENUATOR APPLICATIONS.

Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C

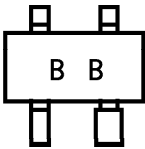


Weight : 0.013g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 10\mu A$	50	—	—	V
Reverse Current	I_R	$V_R = 50V$	—	—	0.1	μA
Forward Voltage	V_F	$I_F = 50mA$	—	0.95	—	V
Total Capacitance	C_T	$V_R = 50V, f = 1MHz$	—	0.25	—	pF
Series Resistance	r_s	$I_F = 10mA, f = 100MHz$	—	3.5	—	Ω

Marking



961001EAA2

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